

**Basic Structure Of Quantum Devices And Process For
Manufacturing Same**

ABSTRACT

5 Structure (Strc) that is capable of forming a quantum device,
comprising: a silicon carrier substrate (Car); a first layer
(Si-L1) of ^{28}Si silicon isotope; a layer (Ox) of silicon oxide;
a second layer (Si-L2) of ^{28}Si silicon isotope, the structure
10 being formed by the carrier substrate (Car), the first layer
(Si-L1) of ^{28}Si silicon isotope, the layer (Ox) of silicon
oxide, and the second layer (Si-L2) of ^{28}Si silicon isotope,
stacked in this order, in which the first layer (Si-L1) and
the second layer (Si-L2) of ^{28}Si silicon isotope are each
15 formed from at least 99.92% ^{28}Si silicon isotope.

Fig. 3